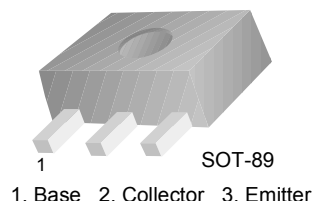


# KSA1201

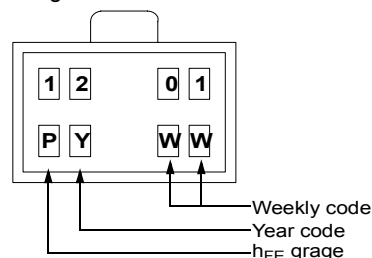
## PNP Epitaxial Silicon Transistor

### Power Amplifier

- Collector-Emitter Voltage:  $V_{CEO} = -120V$
- $f_T = 120MHz$
- Collector Power Dissipation  $P_C = 1 \sim 2W$  : Mounted on Ceramic Board
- Complement to KSC2881



Marking



### Absolute Maximum Ratings $T_a = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{CBO}$	Collector Base Voltage	-120	V
$V_{CEO}$	Collector-Emitter Voltage	-120	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current	-800	mA
$I_B$	Base Current	-160	mA
$P_C$	Collector Power Dissipation	500	mW
$P_C^*$		1,000	mW
$T_J$	Junction Temperature	150	$^\circ C$
$T_{STG}$	Storage Temperature	-55 ~ 150	$^\circ C$

\* Mounted on Ceramic Board (250mm<sup>2</sup> x 0.8mm)

### Electrical Characteristics $T_a = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
$BV_{CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -10mA, I_B = 0$	-120			V
$BV_{EBO}$	Emitter-Base Breakdown Voltage	$I_E = -1mA, I_C = 0$	-5			V
$I_{CBO}$	Collector Cut-off Current	$V_{CB} = -120V, I_E = 0$			-100	nA
$I_{EBO}$	Emitter Cut-off Current	$V_{BE} = -5V, I_C = 0$			-100	nA
$h_{FE}$	DC Current Gain	$V_{CE} = -5V, I_C = -100mA$	80		240	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -500mA, I_B = -50mA$			-1.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$V_{CE} = -5V, I_C = -500mA$			-1.0	V
$f_T$	Current Gain Bandwidth Product	$V_{CE} = -5V, I_C = -100mA$		120		MHz
$C_{ob}$	Output Capacitance	$V_{CB} = -10V, I_E = 0, f = 1MHz$			30	pF

**$h_{FE}$  Classification**

Classification	O	Y
$h_{FE}$	80 ~ 160	120 ~ 240

**Package Marking and Ordering Information**

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
1201	KSA1201	SOT-89	13"	--	4,000

## Typical Performance Characteristics

Figure 1. Static Characteristic

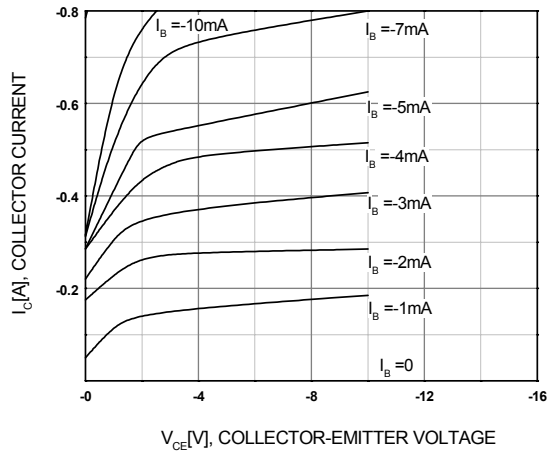


Figure 2. DC Current Gain

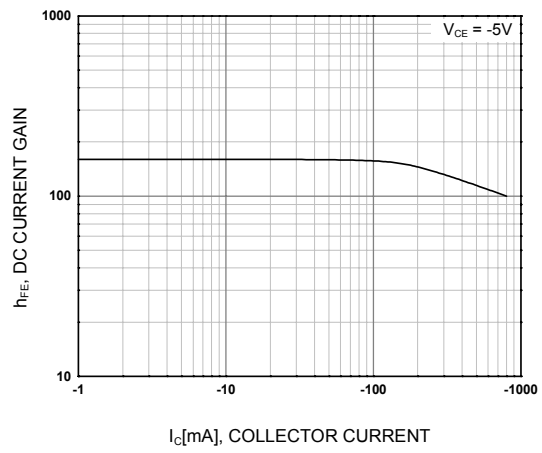


Figure 3. Collector-Emitter Saturation Voltage

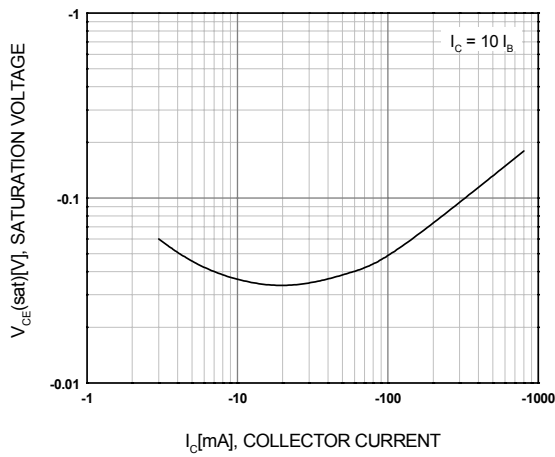


Figure 4. Base-Emitter On Voltage

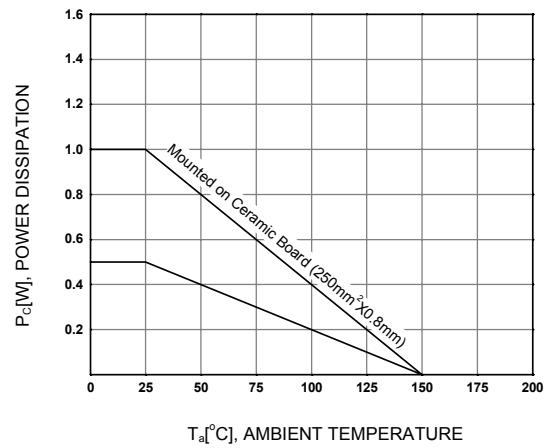


Figure 5. Safe Operating Area

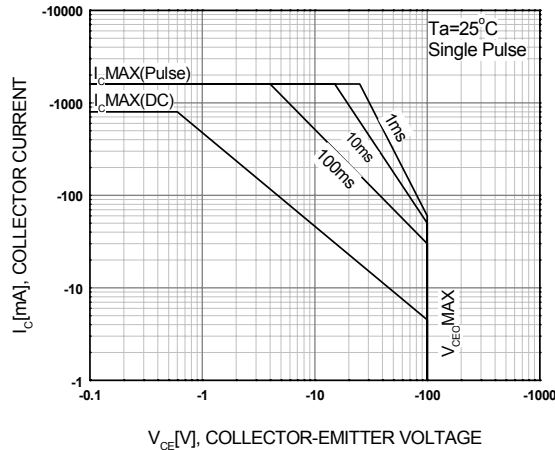
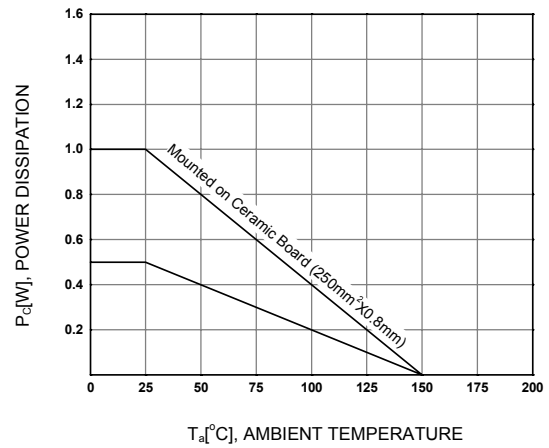
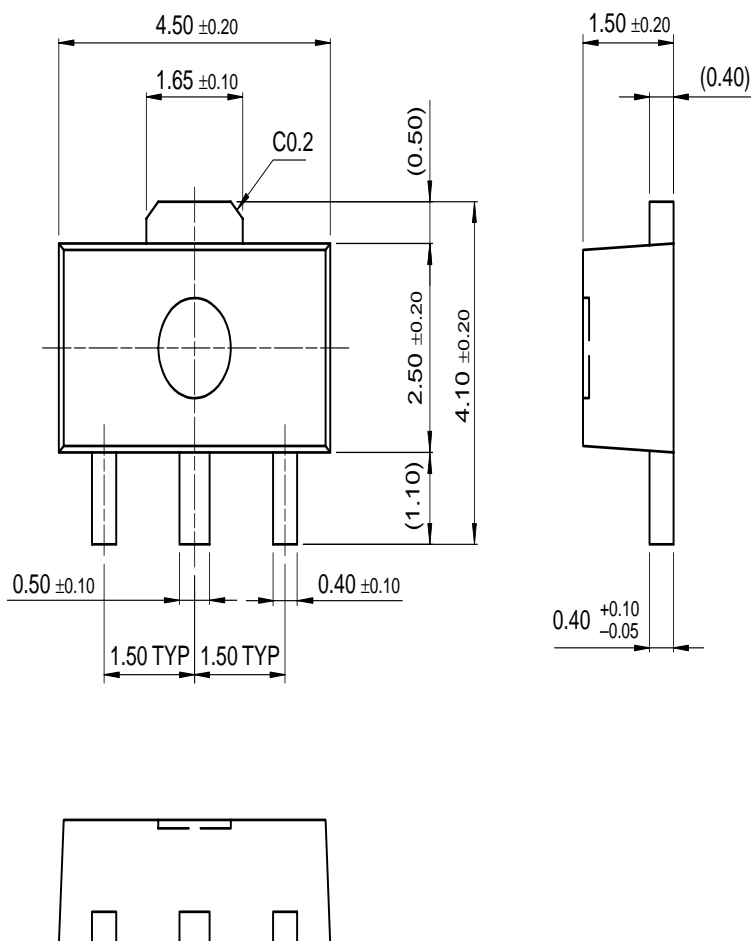


Figure 6. Power Derating



## Mechanical Dimensions

# SOT-89



### Dimensions in Millimeters

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